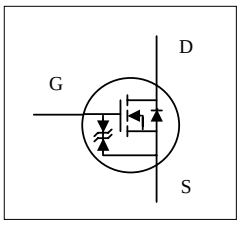
AP9T18GEH/J

Pb Free Plating Product

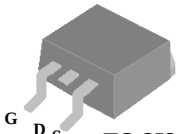
Advanced Power Electronics Corp.

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

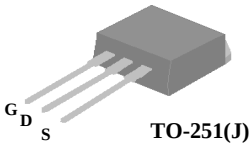
- ▼ G-S Diode embedded
- ▼ Capable of 2.5V gate drive
- ▼ Surface mount package
- ▼ RoHS Compliant



BV_{DSS}	20V
$R_{DS(ON)}$	14mΩ
I_D	40A



TO-252(H)



TO-251(J)

Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, ultra low on-resistance and cost-effectiveness.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 4.5V	40	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 4.5V	25	A
I_{DM}	Pulsed Drain Current[1]	160	A
P_D@T_C=25℃	Total Power Dissipation	31	W
	Linear Derating Factor	0.25	W/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter		Value	Units
Rthj-c	Thermal Resistance Junction-case	Max.	4	℃/W
Rthj-a	Thermal Resistance Junction-ambient	Max.	110	℃/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	20	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25℃, I_D=1mA	-	0.02	-	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=4.5V, I_D=20A	-	-	14	mΩ
		V_{GS}=2.5V, I_D=10A	-	-	28	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	0.4	-	1.5	V
g_{fs}	Forward Transconductance	V_{DS}=5V, I_D=20A	-	20	-	S
I_{DSS}	Drain-Source Leakage Current (T_j=25°C)	V_{DS}=20V, V_{GS}=0V	-	-	1	uA
	Drain-Source Leakage Current (T_j=150°C)	V_{DS}=16V ,V_{GS}=0V	-	-	25	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±12V	-	-	±30	uA
Q_g	Total Gate Charge[2]	I_D=20A	-	16	26	nC
Q_{gs}	Gate-Source Charge	V_{DS}=16V	-	2	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=4.5V	-	6	-	nC
$t_{d(on)}$	Turn-on Delay Time[2]	V_{DS}=10V	-	8	-	ns
t_r	Rise Time	I_D=20A	-	84	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=1.0Ω,V_{GS}=5V	-	19	-	ns
t_f	Fall Time	R_D=0.5Ω	-	14	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	1080	1730	pF
C_{oss}	Output Capacitance	V_{DS}=20V	-	205	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	145	-	pF
R_g	Gate Resistance	f=1.0MHz	-	3.6	5.4	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=20A, V_{GS}=0V	-	-	1.2	V
t_{rr}	Reverse Recovery Time[2]	I_S=20A, V_{GS}=0V,	-	26	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	19	-	nC

Notes:

1.Pulse width limited by safe operating area.

2.Pulse width ≤300us , duty cycle ≤2%.

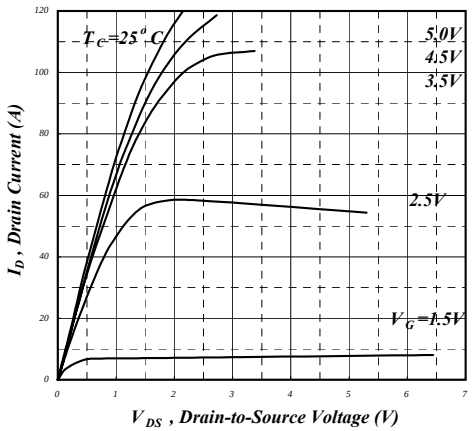


Fig 1. Typical Output Characteristics

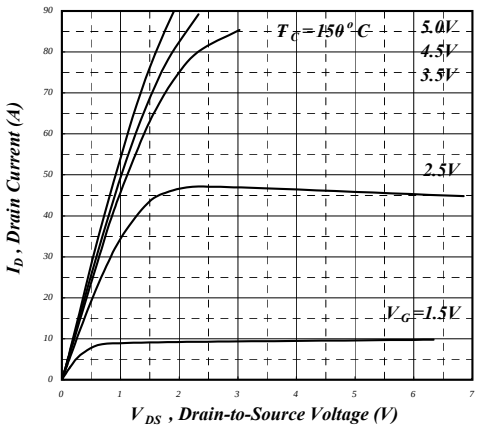


Fig 2. Typical Output Characteristics

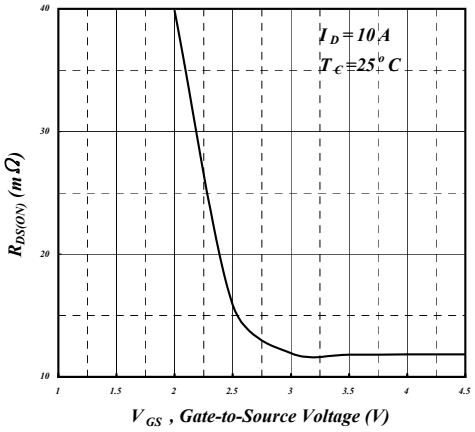


Fig 3. On-Resistance v.s. Gate Voltage

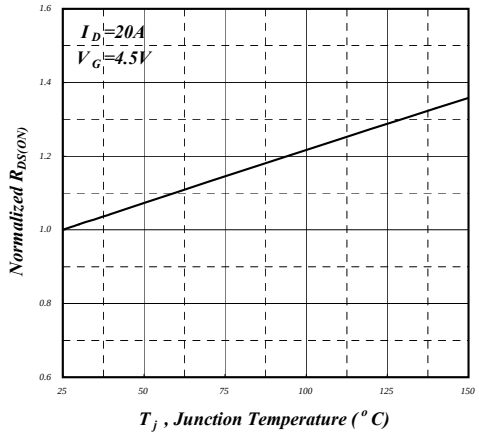


Fig 4. Normalized On-Resistance v.s. Junction Temperature

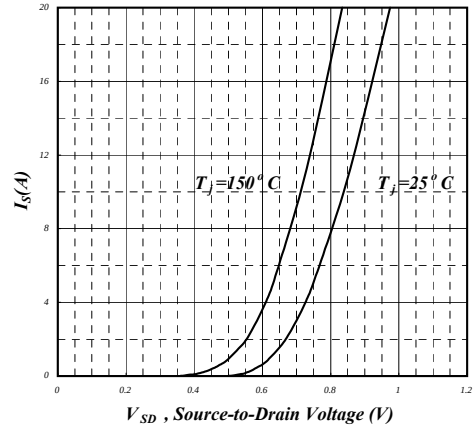


Fig 5. Forward Characteristic of Reverse Diode

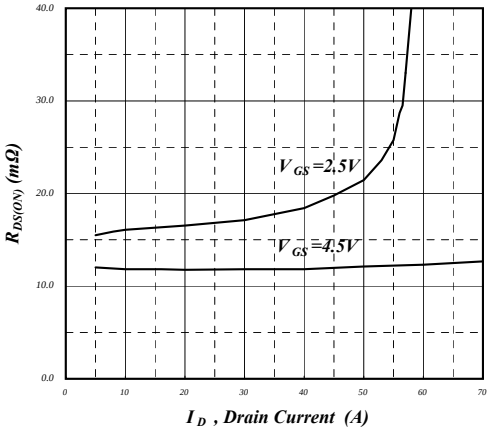


Fig 6. On-Resistance vs. Drain Current

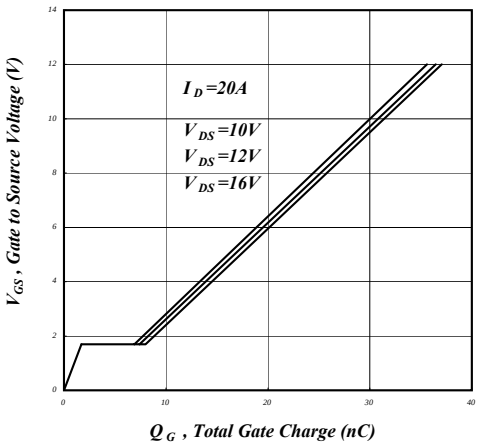


Fig 7. Gate Charge Characteristics

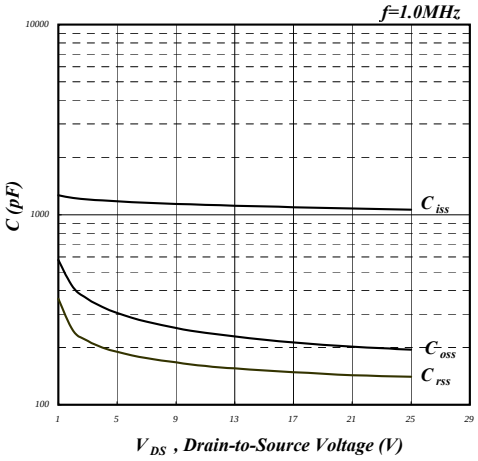


Fig 8. Typical Capacitance Characteristics

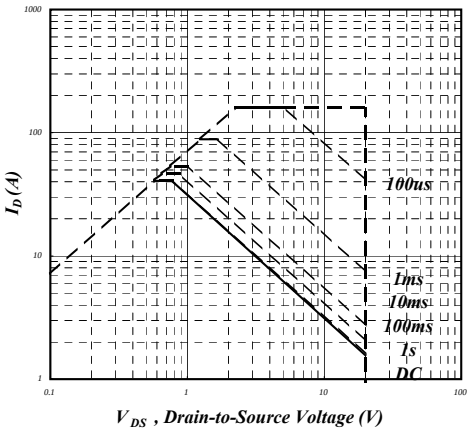


Fig 9. Maximum Safe Operating Area

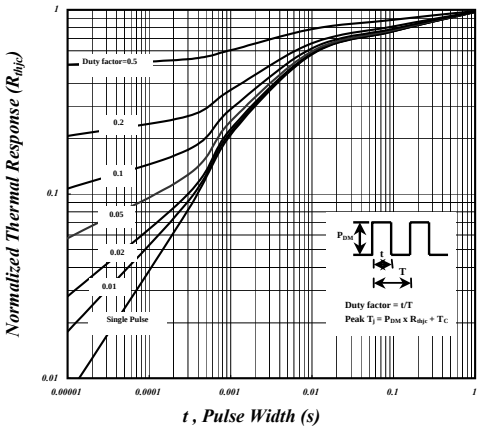


Fig 10. Effective Transient Thermal Impedance

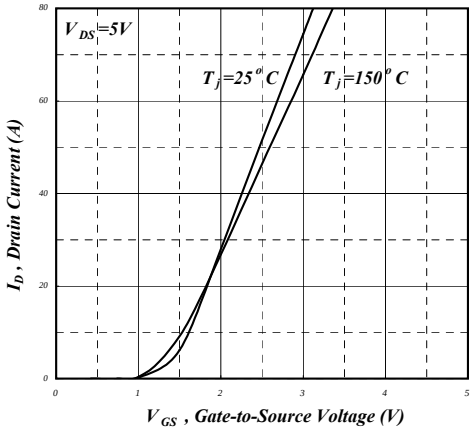


Fig 11. Transfer Characteristics

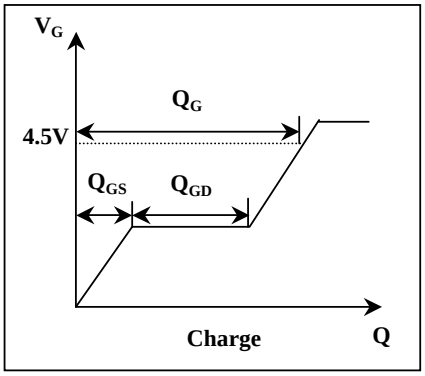


Fig 12. Gate Charge Waveform